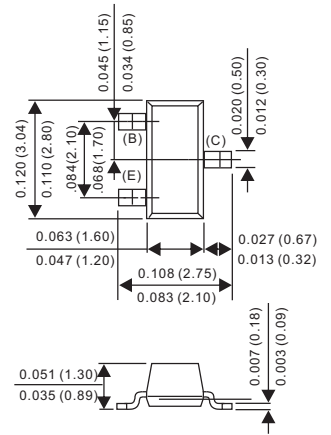
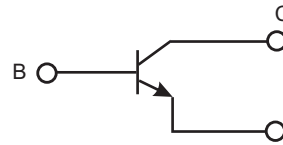


FEATURES

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)

Marking

Type number	Marking code
BC807-16	5A
BC807-25	5B
BC807-40	5C


MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current — Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{slg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = -10\mu A, I_E = 0$	-50		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10mA, I_B = 0$	-45		V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -1\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -45V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -40V, I_B = 0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100	600	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	100		MHz

CLASSIFICATION OF h_{FE}

RANK	BC807-16	BC807-25	BC807-40
RANGE	100-250	160-400	250-600

TYPICAL CHARACTERISTICS

